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A journal on the chemical, electronic, optical and mechanical properties of glasses, amorphous semiconductors and metals, sol–gel materials, the liquid state of these solids and the processes by which they are formed

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Review Articles, Research Papers, Comments and Letters on chemical, electronic, optical, mechanical, structural and fracture properties of non-crystalline materials including glasses, amorphous semiconductors, metals (alloys) and sol–gel materials which form glasses, the liquid state of all materials from which non-crystalline solids can be formed, and the processes for the formation of non-crystalline solids are accepted.

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